

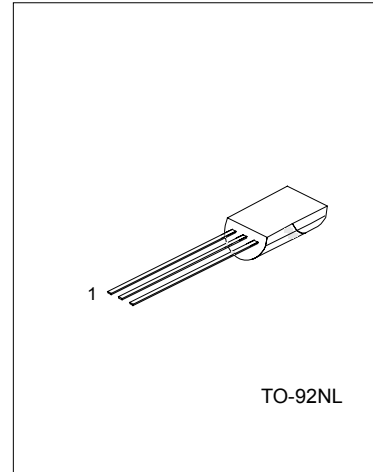
UTC 2SC2328A

NPN EPITAXIAL SILICON TRANSISTOR

AUDIO POWER AMPLIFIER

FEATURES

- *Collector Dissipation $P_c=1$ W
- *3 W Output Application
- *Complement of 2SA928A



1: EMITTER 2: COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EB0}	5	V
Collector dissipation	P _c	1	W
Collector current	I _c	2	A
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV _{CB0}	I _c =100μA, I _E =0	30			V
Collector-emitter breakdown voltage	BV _{CEO}	I _c =10mA, I _B =0	30			V
Emitter-base breakdown voltage	BV _{EB0}	I _E =1mA, I _c =0	5			V
Collector cut-off current	I _{CB0}	V _{CB} =30V, I _E =0			100	nA
Emitter cut-off current	I _{EB0}	V _{BE} =5V, I _c =0			100	nA
DC current gain(note)	h _{FE}	V _{CE} =2V, I _c =500mA	100		320	
Base-emitter on voltage	V _{BE(on)}	V _{CE} =2V, I _c =500mA			1	V
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =1.5A, I _B =0.03A			2	V
Output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		30		pF
Current gain bandwidth product	f _t	V _{CE} =2V, I _c =500mA		120		MHz

CLASSIFICATION OF hFE

RANK	O	Y
RANGE	100-200	160-320

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1

QW-R211-008,A

TYPICAL CHARACTERISTIC CURVES

